SCP20120DN4

20A, 1200V SiC Schottky Barrier Diode

Features

- Low Forward Voltage Drop: V_F=1.55V (typical @ I_F=10A)
- Reverse Voltage: V_{RRM}=1200V
- Avalanche Energy Rated
- High Surge Capability
- Low Power Loss and High Efficiency
- Silicon Carbide Substrate

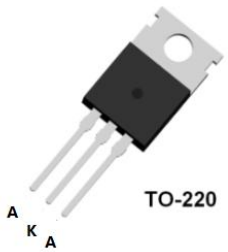
Applications

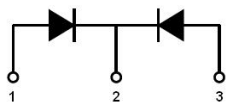
- Switching Power Supply
- Solar Inverter
- Power Factor Correction
- Uninterruptible Power Supply

Description

The SCP20120DN4 is a SiC schottky barrier diode. It is base on silicon carbide material, and its switching behavior is independent with temperature. The device has superfast recovery property and lower forward voltage drop, it can be used in switching power supply, solar inverter, PFC and UPS.

Package Type & internal Circuit





1. Anode 2.Cathode 3.Anode

Absolute Maximum Ratings per diode at T_C=25 ℃ unless otherwise noted

Symbol	Parameter		Ratings	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		1200	V
V_{RWM}	Working Peak Reverse Voltage		1200	V
V_R	DC Blocking Voltage		1200	V
$I_{F(AV)}$	Average Rectified Forward Current	per diode at T_C=125℃	10	A
I_{FSM}	Non-repetitive Peak Surge Current	t_p=10ms, half sine wave	60	A
		t_p=200us, square wave	240	A
P_D	Power Dissipation		160	W
T_J	Operating Junction Temperature Range		-55~+175	℃
T_{STG}	Storage Temperature Range		-55~+175	℃

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th\ (J-C)}$	Thermal Resistance, Junction to case	1	℃/W

Electrical Characteristics per diode at T_C=25 ℃ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop	I_F=10A	-	1.55	1.80	V
		I_F=10A, T_C=125℃	-	-	2.55	V
I_R	Reverse Leakage Current	V_R=1200V	-	-	200	uA
C	Total Capacitance	V_R=0V, f=1MHz	-	650	-	pF
		V_R=400V, f=1MHz	-	49	-	
		V_R=800V, f=1MHz	-	40	-	
Q_C	Total Capacitive Charge	V_R=800V, I_F=10A, di/dt=-200A/us	-	33	-	nC

Typical Performance Characteristics

Fig. 1. Typical Characteristics: V_F vs. I_F

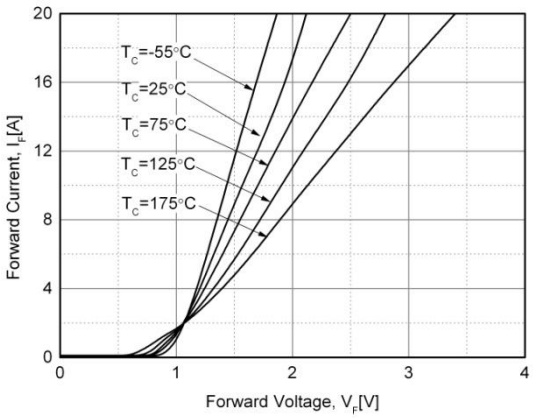


Fig. 2. Typical Characteristics: V_R vs. I_R

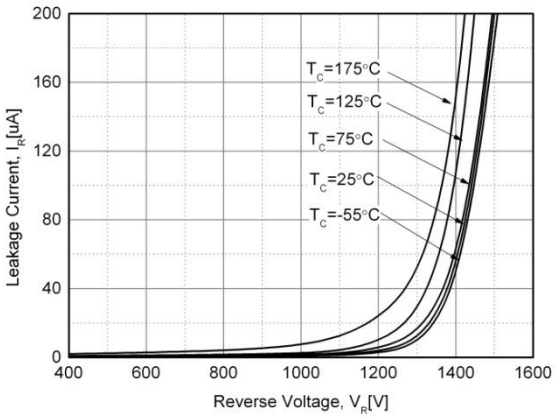


Fig. 3. Typical Characteristics: V_R vs. Q_C

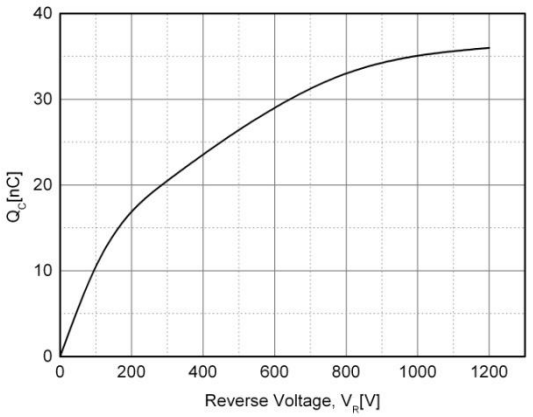
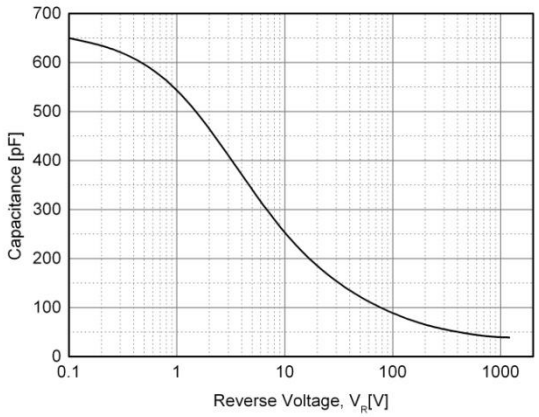


Fig. 4. Typical Characteristics: V_R vs. Capacitance



Package Dimensions

TO-220

(Dimensions in Millimeters)